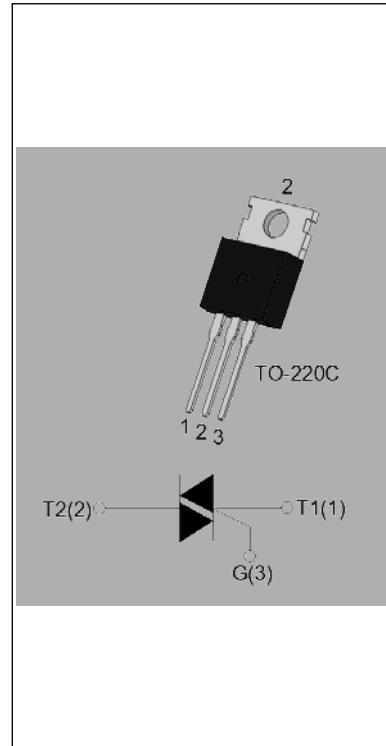




The T2035H-8C triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T2035H-8C provides a very high switching capability up to junction temperatures of 150°C. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	20	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	35/35/35	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
RMS on-state current ($T_c = 0124^\circ C$)	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	200	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		220	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	200	A^2s
Critical rate of rise of on-state current ($I_G=2mA$, $f=100Hz$, $T_j=150^\circ C$)	dI/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=150^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W



Peak pulse voltage ($T_j=25^\circ C$; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV
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($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150^\circ C$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
I_H				80	
dV/dt	$V_D=540V$ Gate Open $T_j=150^\circ C$		MIN.	1500	V/ μ s
$(dI/dt)c$	$(dV/dt)c=20V/\mu s$, $T_j=150^\circ C$		MIN.	20	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25^\circ C$	TYP.	8	μ s	
t_{off}			70		

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=28A t_p=380\mu s$	$T_j=25^\circ C$	1 .4	V
V_{TO}	Threshold voltage	$T_j=150^\circ C$	0.71	V
R_D	Dynamic resistance	$T_j=150^\circ C$	22	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=150^\circ C$	3 .5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W



T	20	35	H	-8	C
Triacs					C:TO-220C
					<u>8:V_{DRM} /V_{RRM} 1 800V</u>
		<u>35:I_GT1-3 0 35mA</u>			High junction temperature

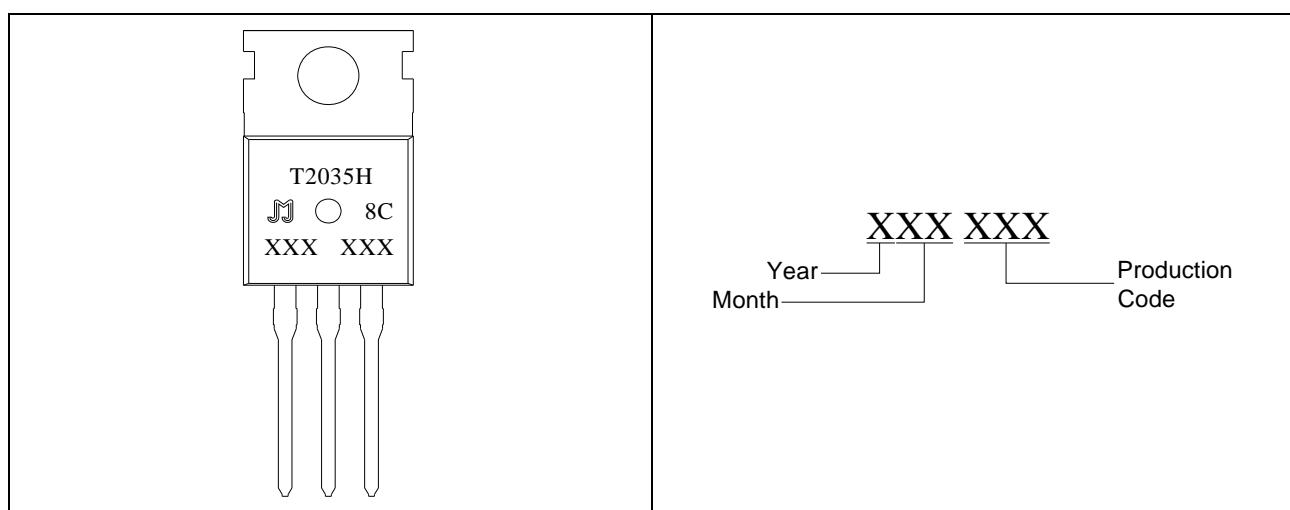




FIG.1 Maximum power dissipation versus RMS on-state current

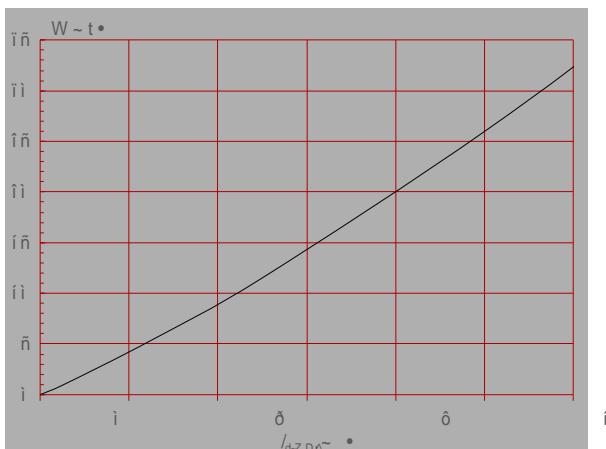


FIG.3: Surge peak on-state current versus number of cycles

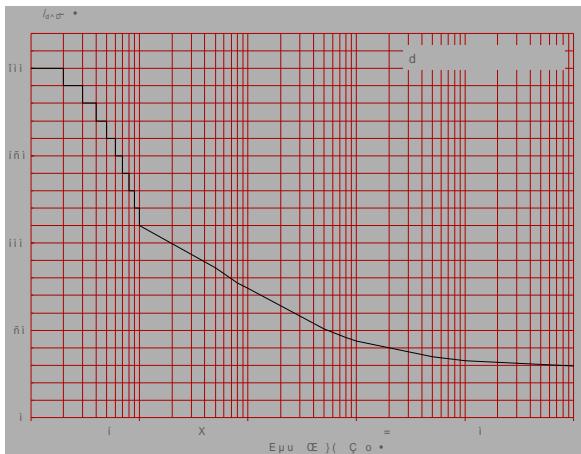


FIG.2: RMS on-state current versus case temperature

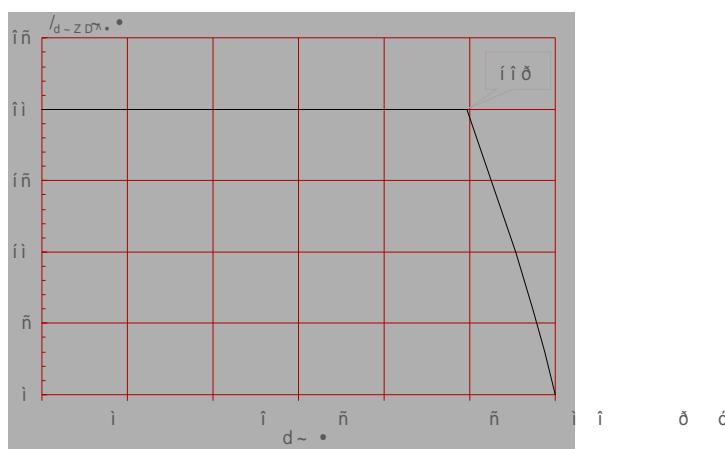
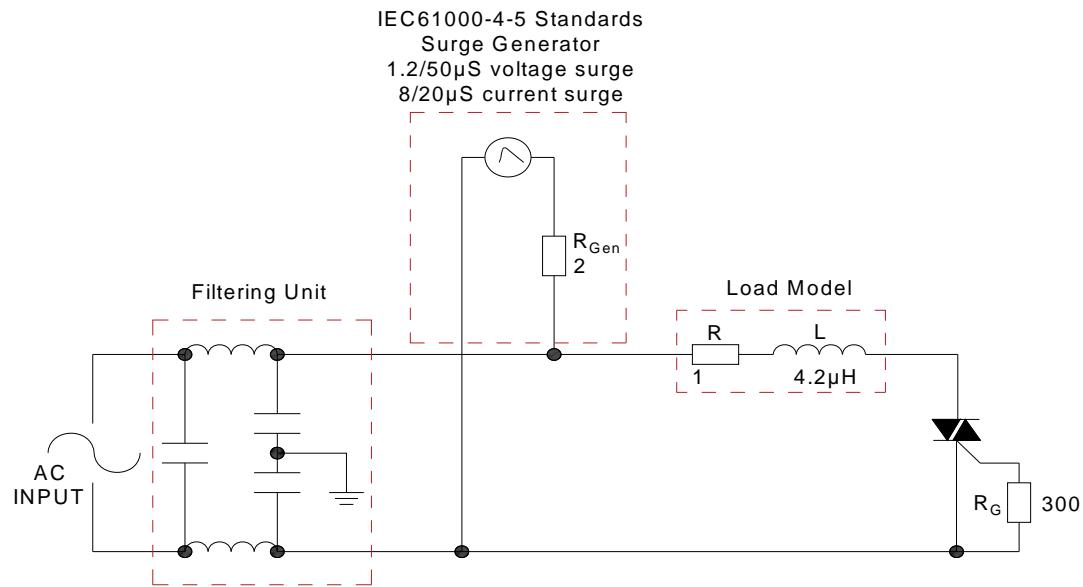


FIG.4: On-state characteristics

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



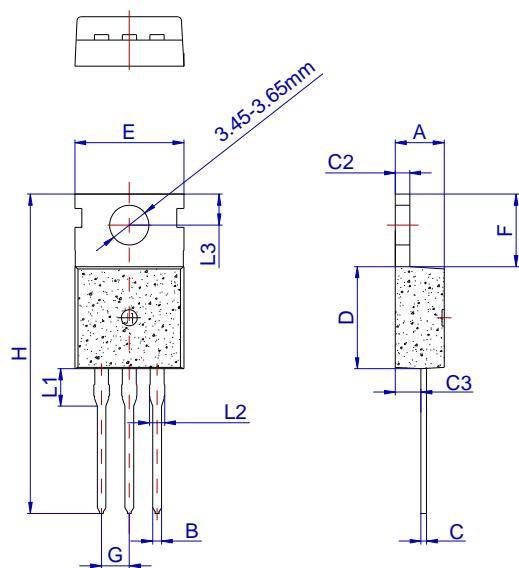
Refer to ÈInstructions for installation of plastic-sealed in-line power devices Èreleased by JieJie



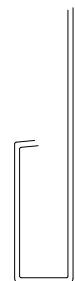
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T2035H-8C	800	35	TO-220C	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116





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